



PRODUCT DATA SHEET

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Datasheet



Resources



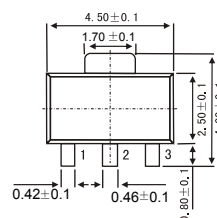
Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

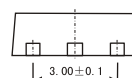
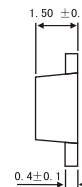
■ Features

- Low noise and high gain
- High power gain
- Large P_{tot}

SOT-89



Unit:mm



- 1.Base
- 2.Collector
- 3.Emitter

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	20	V
Collector - Emitter Voltage	V_{CEO}	12	
Emitter - Base Voltage	V_{EBO}	3	
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	1.2	W
Junction to Ambient Resistance	$R_{th(j-a)}$	62.5	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

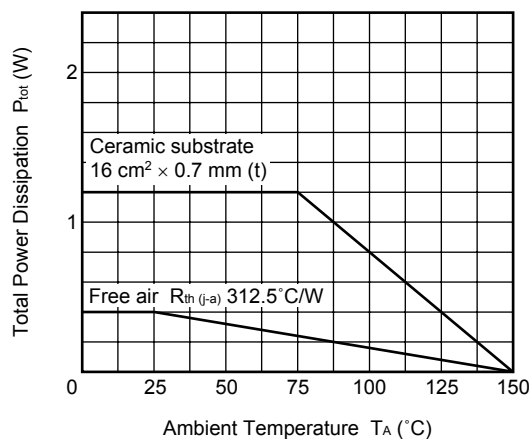
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	20			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	12			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.2	
DC current gain (Note.1)	h_{FE}	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$	50		250	
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}, f = 1 \text{ GHz}$		9		dB
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 7 \text{ mA}, f = 1 \text{ GHz}$		1.1		
		$V_{CE} = 10\text{V}, I_C = 40 \text{ mA}, f = 1 \text{ GHz}$		1.8	3	
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 10\text{V}, I_E = 0, f = 1 \text{ MHz}$			1	pF
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$		6.5		GHz

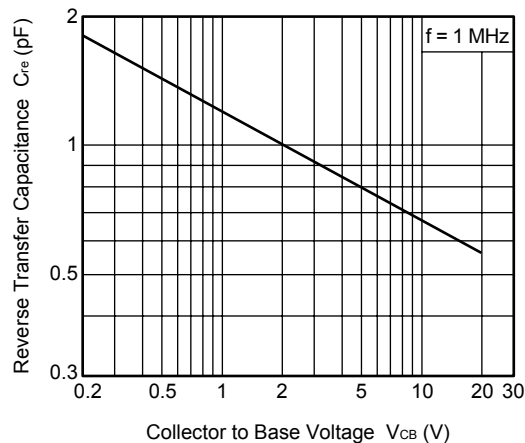
Note.1: Pulse measurement: $PW \leq 350 \mu\text{s}$, Duty Cycle $\leq 2\%$

■ Typical Characteristics

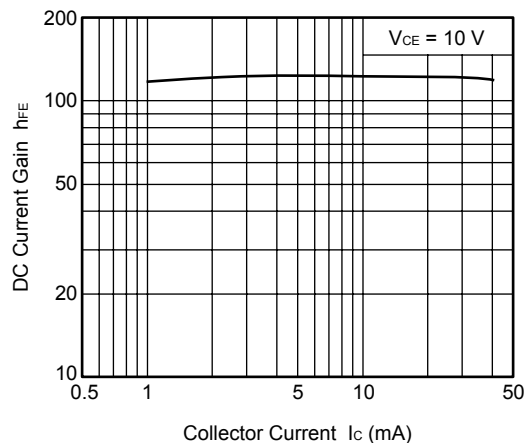
TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE



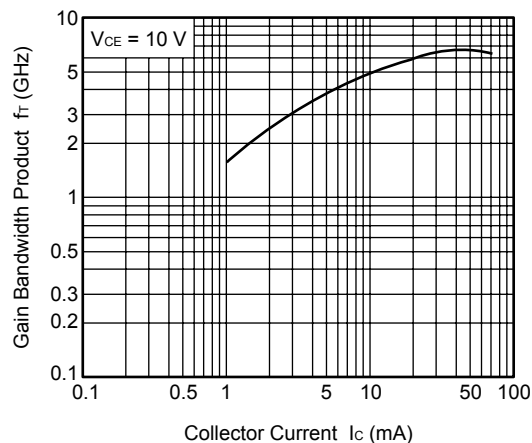
REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE



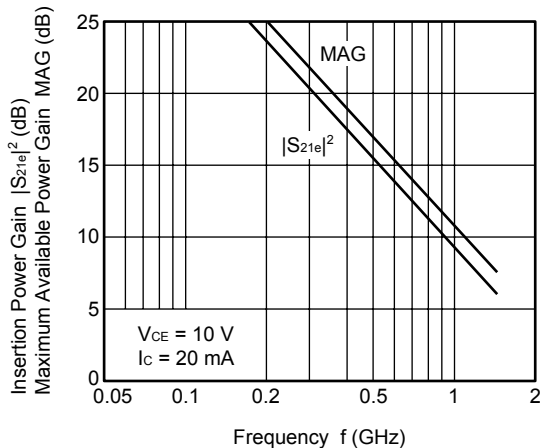
DC CURRENT GAIN vs.
COLLECTOR CURRENT



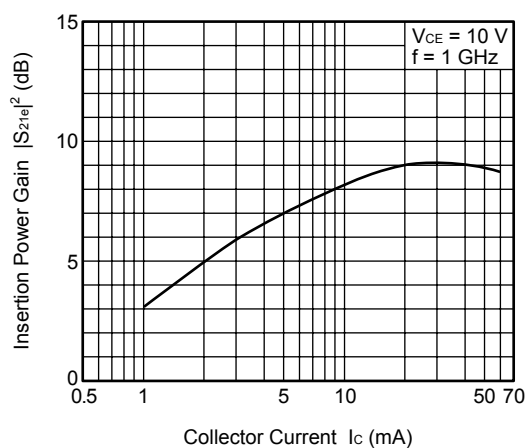
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG
vs. FREQUENCY

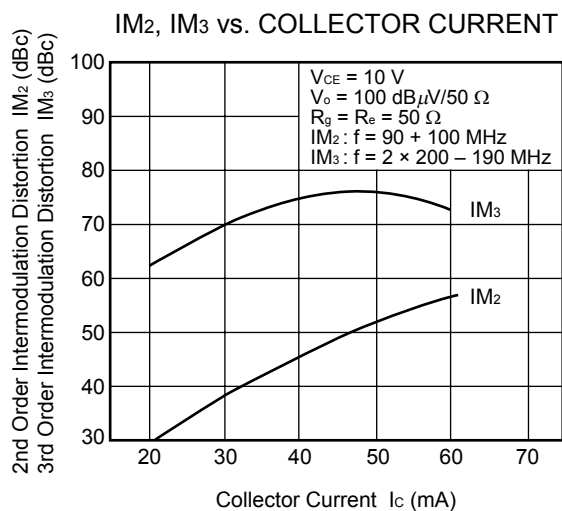
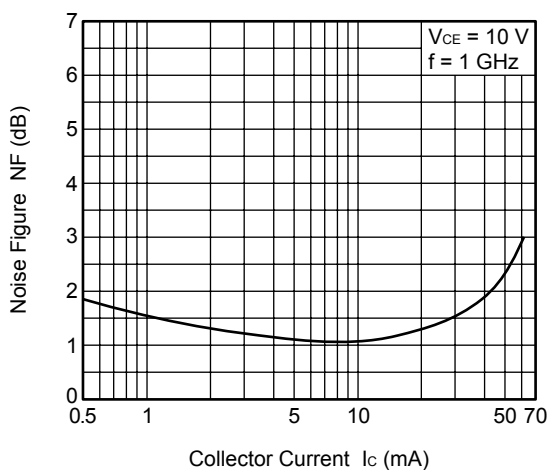


INSERTION POWER GAIN
vs. COLLECTOR CURRENT



■ Typical Characteristics

NOISE FIGURE vs.
COLLECTOR CURRENT



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